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(56) Documents Cited
GB 2250880 A **GB 2136652 A**
US 4870533 A

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(54) Abstract Title
Method for thermal stabilisation of operating conditions in transistors

(57) The invention relates to the field of electronic engineering and can be used for stabilisation of operating conditions in the direct current in electronic devices. The object of the invention is stabilisation of operating conditions in electronic schemes independent of a temperature of the crystal body of the amplifying element and an environmental temperature. This method lets to obtain the object of the invention by using the active non-linear direct current negative feedback.

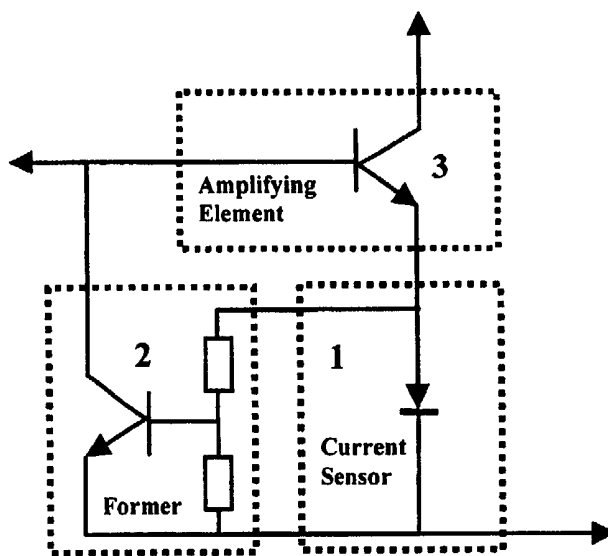


Fig. 1